# MSKSEMI 美森科













**ESD** 

TVS

TSS

MOV

GDI

PLED

PMBT3906MB(MS)

**Product specification** 





#### **Features**

- Low profile package
- Ideal for automated placement
- Complementary to PMBT3904MB(MS) (NPN)
- Power Dissipation of 200mW
- High Stability and High Reliability
- RoHS Compliant

# **Applications**

- amplifying signal
- Electronic switch
- Oscillating circuit
- variable resistance

## **Appearance & Symbol**

PACKAGE OUTLINE	Pin Configuration	Marking
1: Base 2: Emitter 3: Collector	Base	2A



# Absolute Maximum Ratings (T=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-40	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-40	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5	V
Collector Current - Continuous	Ic	-200	mA
Collector Power Dissipation	Pc	200	mW
Thermal Resistance From Junction to Ambient	R <sub>θJA</sub>	625	°C/W
Junction Temperature	TJ	-55 to +150	°C
Junction and Storage Temperature	T <sub>STG</sub>	-55 to +150	°C

#### Electrical Characteristics (T=25℃ unless otherwise noted)

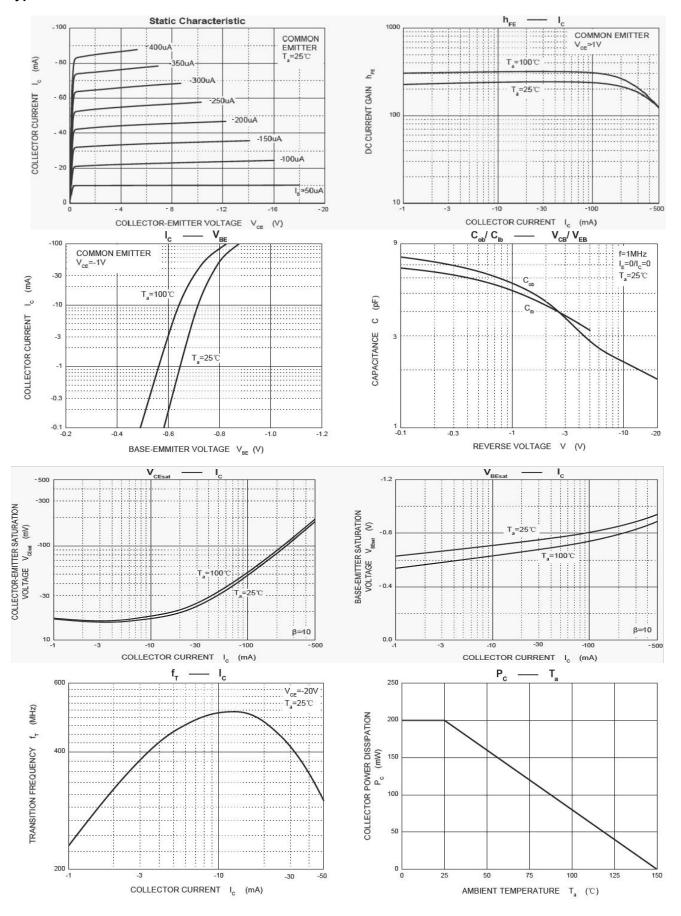
Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =-10uA, I <sub>E</sub> =0	-40		V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =-1mA, I <sub>B</sub> =0	-40		V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =-10uA, I <sub>C</sub> =0	-5		V
Collector cut-off current	I <sub>CEX</sub>	V <sub>CE</sub> =-30V, V <sub>BE(Off)</sub> =-3V		-50	nA
Collector cut-off current	Ісво	V <sub>CB</sub> =-40V, I <sub>E</sub> =0		-100	nA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =-5V, I <sub>C</sub> =0		-100	nA
DC current gain	h <sub>FE(1)</sub>	V <sub>CE</sub> =-1V, I <sub>C</sub> =-10mA	100	300	
	h <sub>FE(2)</sub>	V <sub>CE</sub> =-1V, I <sub>C</sub> =-50mA	60		
	h <sub>FE(3)</sub>	V <sub>CE</sub> =-2V, I <sub>C</sub> =-100mA	30		
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-50mA, I <sub>B</sub> =-5mA		-0.3	V
Base -emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =-50mA, I <sub>B</sub> =-5mA		-0.95	V
Transition frequency	f⊤	V <sub>CE</sub> =-20V, I <sub>C</sub> =-10mA,f=100MHz	300		MHz
Delay time	td	Vcc=-3V.VBE=-0.5V		35	nS
Rise time	tr	I <sub>C</sub> =-10mA, I <sub>B1</sub> =I <sub>B2</sub> =-1mA		35	nS
Storage time	ts	Vcc=-3V,Ic=-10mA		225	nS
Fall time	tf	I <sub>B1</sub> =I <sub>B2</sub> =-1mA		75	nS

### Classification of hFE

Range	100-300
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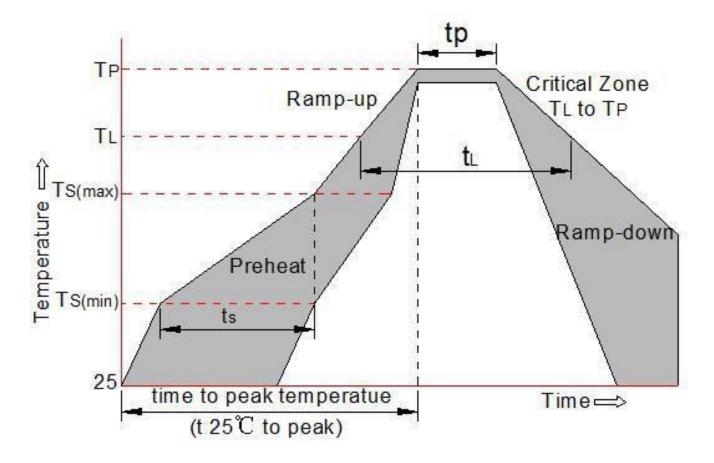
#### **Typical Characteristics**





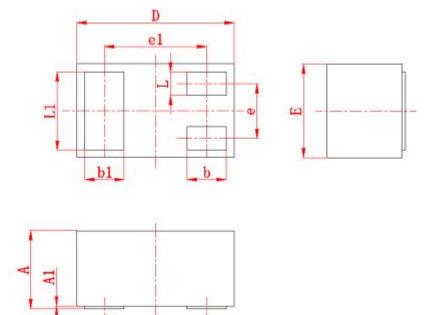
### Soldering parameters

Reflow Condition		Pb-Free assembly (see as bellow)
	-Temperature Min (T <sub>s(min)</sub> )	+150℃
Pre Heat	-Temperature Max(T <sub>s(max)</sub> )	+200℃
riorioat	-Time (Min to Max) (ts)	60-180 secs.
Average	Average ramp up rate (Liquid us Temp (T∟) to peak)	
	T <sub>s(max)</sub> to T <sub>L</sub> - Ramp-up Rate	
	-Temperature(T <sub>L</sub> ) (Liquid us)	+217℃
Reflow	-Temperature(t <sub>∟</sub> )	60-150 secs.
	Peak Temp (T <sub>p</sub> )	
Tir	me within 5℃ of actual Peak Temp (tp)	30 secs. Max
Ramp-down Rate		6°C/sec. Max
Time 25℃ to Peak Temp (T <sub>P</sub> )		8 min. Max
Do not exceed		+260℃



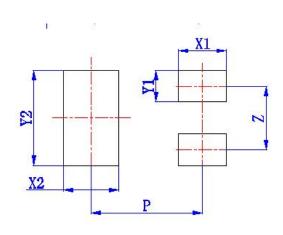


## Package mechanical data



Cumbal	Millimeters		
Symbol	min	max	
А	0.4	0.5	
A1	0	0.05	
D	0.9	1.1	
E	0.55	0.65	
е	(0.35)		
e1	(0.65)		
b	0.2	0.3	
b1	0.2	0.3	
L	0.1 0.2		
L1	0.45 0.55		

## **Suggested Land Pattern**



Symbol	Dimension in Millimeters	
	typ	
X1	(0.3)	
X2	(0.35)	
Y1	(0.2)	
Y2	(0.6)	
Z	(0.4)	
Р	(0.7)	

### **REEL SPECIFICATION**

P/N	PKG	QTY
MMBT3906MB(MS)	DFN1006-3	10000



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